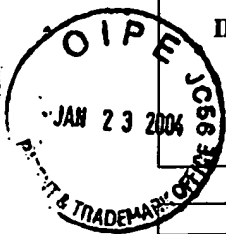


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U.S. PATENT DOCUMENTS						
Examiner's Initials	Document Number	Publication Date	Inventor	Class	Subclass	Filing Date If Appropriate

FOREIGN PATENT DOCUMENTS								
Examiner's Initials	Document Number	Publication Date	Country	Class	Subclass	Translation		
						Yes	No	
QNB	56-92577	07-27-81	Japan	X	X			X
QNB	57-45583	03-15-82	Japan					X
QNB	57-52071	03-27-82	Japan					✓
QNB	57-52072	03-27-82	Japan					✓
QNB	57-52073	03-27-82	Japan					✓
QNB	58-50577	03-25-83	Japan					✓
QNB	61-156780	07-16-86	Japan					✓
QNB	63-188938	08-04-88	Japan					
QNB	02-263668	10-26-90	Japan				ABS	
QNB	03-035568	02-15-91	Japan				ABS	
QNB	06-067044	03-11-94	Japan				ABS	
QNB	06-045648	02-18-94	Japan				ABS	
QNB	07-199829	04-08-95	Japan				ABS	
QNB	08-008217	01-12-96	Japan				ABS	
QNB	08-255929	10-01-96	Japan				ABS	
QNB	09-129974	05-16-97	Japan				ABS	
QNB	09-199419	07-31-97	Japan				ABS	
QNB	WO 97/44612	11-27-97	PCT				ABS	
QNB	10-125929	05-15-98	Japan				ABS	
QNB	10-265297	10-06-98	Japan	X	X		AB	

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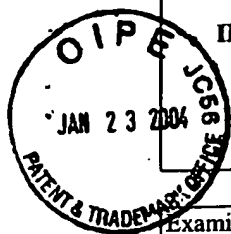
FOREIGN PATENT DOCUMENTS

Examiner's Initials	Document Number	Publication Date	Country	Class	Subclass	Translation	
						Yes	No
QWB	10-270801	10-09-98	Japan			ABS	
QWB	10-312971	11-24-98	Japan			ABS	
QWB	10-321910	12-04-98	Japan			ABS	
QWB	11-026883	01-29-99	Japan			ABS	
QWB	11-075019	03-16-99	Japan			ABS	
QWB	11-177138	07-02-99	Japan			ABS	
QWB	11-238687	08-31-99	Japan			ABS	
QWB	11-251253	09-17-99	Japan			ABS	
QWB	11-274568	10-08-99	Japan			ABS	
QWB	11-312840	11-09-99	Japan			ABS	
QWB	11-514136	11-30-99	Japan			ABS	
QWB	11-346004	12-14-99	Japan			ABS	
QWB	2000-012976	01-14-00	Japan			ABS	
QWB	2000-068593	03-03-00	Japan			ABS	
QWB	2000-150391	05-30-00	Japan			ABS	
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QWB	2000-223417	08-11-00	Japan			ABS	
QWB	2000-332343	11-30-00	Japan			ABS	
QWB	2001-085738	03-30-01	Japan			ABS	
QWB	2001-217503	08-10-01	Japan			ABS	
QWB	2002-185660	12-12-02	Japan	X	X	ABS	

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Examiner's Initials	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)
QWB	Zheleva et al., Pendeo-epitaxy - a new approach for lateral growth of gallium nitride structures, MRS Internet J. Nitride Semicond. Res. 4S1, G3.38 (1999).

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Examiner's Initials	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)
QWB	Kapolnek et al., <i>Spatial control of InGaN luminescence by MOCVD selective epitaxy</i> , Journal of Crystal Growth, 189/190 (1998) pp. 83-86.
QWB	J. Wang et al., <i>Fabrication of nanoscale structures of InGaN by MOCVD lateral overgrowth</i> , Journal of Crystal Growth 197 (1999), pp. 48-53.
QWB	Raj Singh et al., <i>Selective Area Growth of GaN Directly on (0001) Sapphire by the HVPE Technique</i> , MRS Internet Journal Nitride Semiconductor Research, 3, 13 (1998), pp. 1-4.
QWB	Zhigang Mao, et al., <i>Defects in GaN Pyramids Grown on Si(111) Substrates by Selective Lateral Overgrowth</i> , Materials Research Society Meeting in Boston, Mass. (1998), pp. 1-6.
QWB	Tachibani et al, <i>Selective growth of InGaN quantum dot structures and their microphotoluminescence at room temperature</i> , Applied Physics Letters, Vol. 76, No. 22, May 29, 2000, pp. 3212-3214.
QWB	Yang et al., <i>Single-crystal GaN pyramids grown on (1 1 1)Si substrates by selective lateral overgrowth</i> , Journal of Crystal Growth, Volume 204, (1999), pp. 247-418.

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